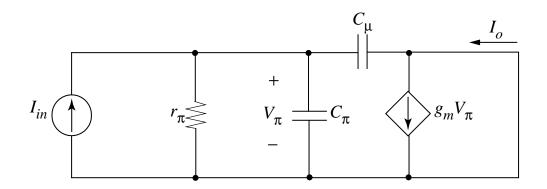
## **Frequency Response of Transistor Amplifiers**

■ Simplest case: CE short-circuit current gain  $A_i(j\omega)$  as a function of frequency



Kirchhoff's current law at the output node:

$$I_o = g_m V_{\pi} - V_{\pi} j \omega C_{\mu}$$

Kirchhoff's current law at the input node:

$$I_s = \frac{V_{\pi}}{Z_{\pi}} + V_{\pi} j \omega C_{\mu}$$
 where  $Z_{\pi} = r_{\pi} || \left( \frac{1}{j \omega C_{\pi}} \right)$ 

■ Solving for  $V_{\pi}$  at the input node:

$$V_{\pi} = \frac{I_{s}}{(1/Z_{\pi}) + j\omega C_{\mu}}$$

## **Short-Circuit Gain Frequency Response**

■ Substituting  $V_{\pi}$  into the output node equation--

$$\frac{I_o}{I_s} = \frac{g_m Z_{\pi} \left(1 - \frac{j\omega C_{\mu}}{g_m}\right)}{1 + j\omega C_{\mu} Z_{\pi}}$$

■ Substituting for  $Z_{\pi}$  and simplifying --

$$\frac{I_o}{I_s} = \frac{g_m r_{\pi} \left(1 - \frac{j\omega C_{\mu}}{g_m}\right)}{1 + j\omega r_{\pi} (C_{\pi} + C_{\mu})} = \frac{\beta_o \left(1 - \frac{j\omega C_{\mu}}{g_m}\right)}{1 + j\omega r_{\pi} (C_{\pi} + C_{\mu})} = \beta_o \left[\frac{1 - j\frac{\omega}{\omega_z}}{1 + j\frac{\omega}{\omega_p}}\right]$$

Current gain has one pole:

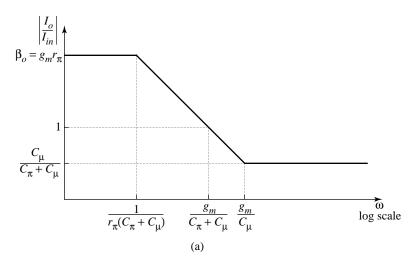
$$\omega_p = (r_{\pi}(C_{\pi} + C_{\mu}))^{-1}$$

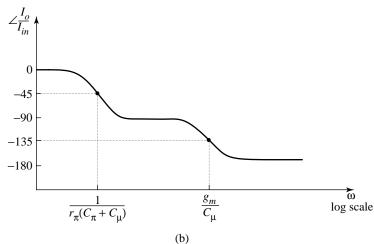
and one zero

$$\omega_z = (g_m^{-1} C_{\mu})^{-1} \gg \omega_p$$

## **Bode Plot of Short-Circuit Current Gain**

■ Note low frequency magnitude of gain is  $\beta_o$ 





■ Frequency at which current gain is reduced to 0 dB is defined as the **transition** frequency  $\omega_T$ . Neglecting the zero,

$$\omega_T = \frac{g_m}{(C_{\pi} + C_{\mu})}$$

## **Transition Frequency of the Bipolar Transistor**

■ Dependence of transition time  $\tau_T = \omega_T^{-1}$  on the bias collector current  $I_C$ :

$$\tau_T = \frac{1}{\omega_T} = \frac{C_{\pi} + C_{\mu}}{g_m} = \frac{g_m \tau_F + C_{jE} + C_{\mu}}{g_m}$$

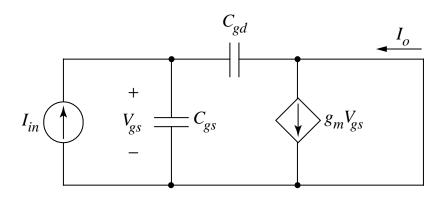
$$\tau_T = \tau_F + \left(\frac{C_{jE} + C_{\mu}}{g_m}\right) = \tau_F + \frac{V_{th}}{I_C}(C_{jE} + C_{\mu})$$

- If the collector current is increased enough to make the second term negligible, then the minimum  $\tau_T$  is the base transit time,  $\tau_F$ . In practice, the  $\omega_T$  decreases at very high values of  $I_C$  due to other effects and the minimum  $\tau_T$  may not be achieved.
- Numerical values of  $f_T = (1/2\pi)\omega_T$  range from 10 MHz for lateral pnp's to 10 GHz for oxide-isolated npn's

Note that the small-signal model is not valid above  $f_T$  (due to distributed effects in the base) and the zero in the current gain is not observed

#### **Common-Source Current Gain**

■ CS amplifier has a non-infinite input *impedance* for  $\omega > 0$  and we can measure its small-signal current gain.



■ Analysis is similar to CE case; result is

$$\frac{I_o}{I_{in}} = \frac{g_m \left(1 - \frac{j\omega C_{gd}}{g_m}\right)}{j\omega (C_{gs} + C_{gd})} \approx \frac{g_m}{\omega (C_{gs} + C_{gd})}$$

■ Transition frequency for the MOSFET is

$$\omega_T \approx \frac{g_m}{C_{gs} + C_{gd}}$$

## **Transition Frequency of the MOSFET**

■ Substitution of gate-source capacitance and transconductance:

$$C_{gs} = \frac{2}{3}WLC_{ox} \times C_{gd}$$
 and  $g_m = \frac{W}{L}\mu_n C_{ox}(V_{GS} - V_{Tn})$ 

$$\omega_T \approx \frac{g_m}{C_{gs}} = \frac{\frac{W}{L} \mu_n C_{ox} (V_{GS} - V_{Tn})}{\frac{2}{3} WLC_{ox}} = \frac{3}{2} \mu_n \left[ \frac{(V_{GS} - V_{Tn})}{L} \right] L$$

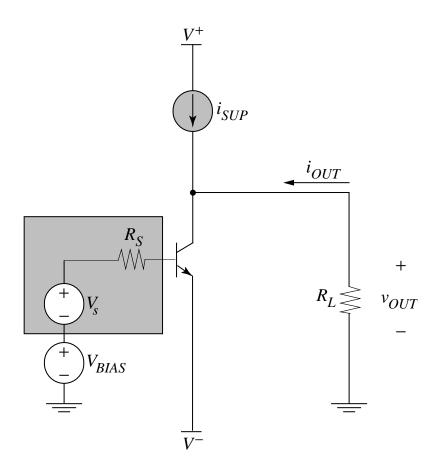
■ The transition time is the inverse of  $\omega_T$  and can be written as the average time for electrons to drift from source to drain

$$\tau_T = \frac{L}{\mu_n \left[ \frac{2}{3} \frac{(V_{GS} - V_{Tn})}{L} \right]} = \frac{L}{\left| \overline{v_{dr}} \right|}$$

velocity saturation causes  $\tau_T$  to decrease linearly with L; however, submicron MOSFETs have transition frequencies that are approaching those for oxide-isolated BJTs

# **Frequency Response of Voltage Amplifiers**

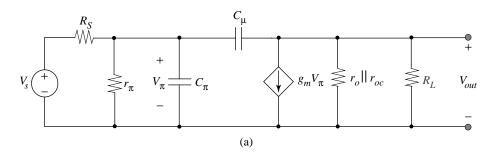
■ Common-emitter amplifier:

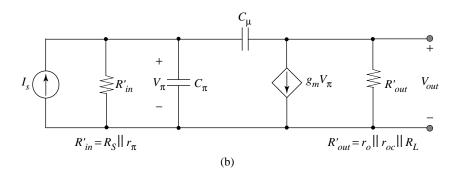


Procedure: substitute small-signal model and perform phasor analysis

## **Brute Force Phasor Analysis**

■ "Exact" analysis: transform into Norton form at input to facilitate nodal analysis





Note that  $C_{cs}$  is omitted, along with  $r_b$ 

Details: see Section 10.4

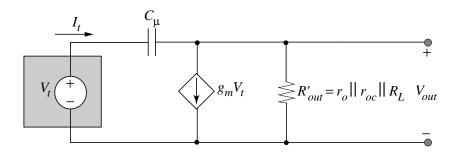
Factor (approximately!) into one high-frequency zero and two poles  $\omega_1 << \omega_2$ 

$$\omega_1^{-1} = (r_{\pi} | |R_S)(C_{\pi} + (1 + g_m r_o) | |r_{oc}| |R_L)C_{\mu}) + (r_o | |r_{oc}| |R_L)C_{\mu}$$

$$\omega_{2}^{-1} = \frac{(r_{o} | |r_{oc}| | R_{L})(r_{\pi} | | R_{S}) C_{\mu} C_{\pi}}{(r_{\pi} | | R_{S})(C_{\pi} + (1 + g_{m} r_{o} | |r_{oc}| | R_{L}) C_{\mu}) + (r_{o} | |r_{oc}| | R_{L}) C_{\mu}}$$

### The Miller Approximation

The "exact" analysis is not particularly helpful for gaining insight into the frequency response ... consider the effect of  $C_{\mu}$  on the input only



neglect the feedforward current  $I_{\mu}$  in comparison with  $g_m V_{\pi}$  ... a good approximation

$$I_t = (V_t - V_o) / Z_{\mu}$$

$$V_o = -g_m V_t R_L / (R_L + R_{out}) = A_{\nu C \mu} V_t$$

where  $A_{\nu C\mu}$  is the low frequency voltage gain across  $C_{\mu}$ 

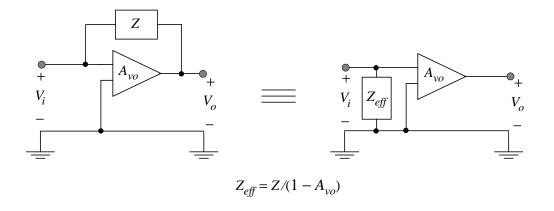
$$I_t = V_t (1 - A_v) / Z_{\mu}$$
  
 $Z_{eff} = V_t / I_t = Z_{\mu} / (1 - A_v)$ 

$$Z_{eff} = \frac{1}{j\omega C_{\mu}} \left( \frac{1}{1 - A_{vC_{\mu}}} \right) = \frac{1}{j\omega (C_{\mu}(1 - A_{vC_{\mu}}))} = \frac{1}{j\omega C_{M}}$$

$$C_M = (1 - A_{vC_u})C_{\mu}$$
 is the Miller capacitor

## **Generalized Miller Approximation**

■ An impedance Z connected across an amplifier with voltage gain  $A_{\nu Z}$  can be replaced by an impedance to ground ... multiplied by  $(1-A_{\nu Z})$ 



■ Common-emitter and common-source:

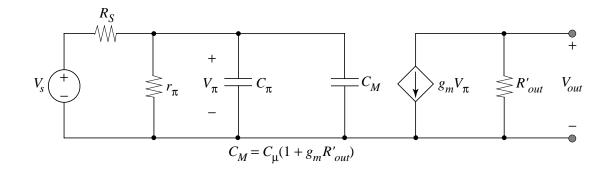
 $A_{\nu Z}$  = large and negative for  $C_{\mu}$  or  $C_{gd}$  --> capacitance at the input is **magnified** 

■ Common-collector and common-drain:

 $A_{vZ} \approx 1$  --> capacitance at the input due to  $C_{\pi}$  or  $C_{gs}$  is greatly **reduced** 

# Voltage Gain vs. Frequency for CE Amplifier Using the Miller Approximation

■ The Miller capacitance is lumped together with  $C_{\pi}$ , which results in a single-pole low-pass RC filter at the input



Transfer function has one pole and no zero after Miller approximation:

$$\omega_{3dB}^{-1} = (r_{\pi} | | R_S)(C_{\pi} + C_M)$$

$$\omega_{3dB}^{-1} = (r_{\pi} | |R_S)[C_{\pi} + (1 + g_m r_o | |r_{oc}| |R_L)C_{\mu}]$$

 $\omega_{3dB}^{-1} \approx \omega_1^{-1}$  from the exact analysis (final term  $R_{out}'C_{\mu}$  is missing)

